



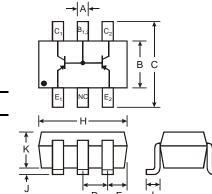
MATCHED PNP SMALL SIGNAL SURFACE MOUNT TRANSISTOR

Features

- **Epitaxial Planar Die Construction**
- Intrinsically Matched PNP Pair (Note 1)
- Small Surface Mount Package
- 2% hFE Matched Tolerance
- Lead Free/RoHS Compliant (Note 3)
- "Green" Device (Note 4 and 5)

Mechanical Data

- Case: SOT-26
- Case Material: Molded Plastic, "Green" Molding Compound, Note 5. UL Flammability Classification Rating 94V-0
- Terminal Connections: See Diagram
- Terminals: Solderable per MIL-STD-202, Method 208
- Lead Free Plating (Matte Tin Finish annealed over Copper leadframe).
- Marking Information: See Page 3
- Ordering Information: See Page 3
- Weight: 0.015 grams (approximate)



	SOT-26										
Dim	Min	Max	Тур								
Α	0.35	0.50	0.38								
В	1.50	1.70	1.60								
C	2.70	3.00	2.80								
D			0.95								
F			0.55								
H	2.90	3.10	3.00								
7	0.013	0.10	0.05								
K	1.00	1.30	1.10								
L	0.35	0.55	0.40								
М	0.10	0.20	0.15								
All Dimensions in mm											

Maximum Ratings @TA = 25°C unless otherwise specified

Characteristic	Symbol	Value	Unit	
Collector-Base Voltage	V _{CBO}	-40	V	
Collector-Emitter Voltage	V _{CEO}	-40	V	
Emitter-Base Voltage	V _{EBO}	-5.0	V	
Collector Current - Continuous	Ic	-200	mA	
Power Dissipation (Note 2)	P _d	225	mW	
Thermal Resistance, Junction to Ambient (Note 2)	$R_{ hetaJA}$	556	°C/W	
Operating and Storage Temperature Range	T _i , T _{STG}	-55 to +150	°C	

Notes:

- Built with adjacent die from a single wafer.
- Device mounted on FR5 PCB: 1.0 x 0.75 x 0.62 in.; pad layout as shown on suggested pad layout document AP02001, which can be found on our 2. website at http://www.diodes.com/datasheets/ap02001.pdf.
- No purposefully added lead.
- Diodes Inc.'s "Green" policy can be found on our website at http://www.diodes.com/products/lead_free/index.php.
- Product manufactured with Date Code 0627 (week 27, 2006) and newer are built with Green Molding Compound. Product manufactured prior to Date Code 0627 are built with Non-Green Molding Compound and may contain Halogens or Sb2O3 Fire Retardants.

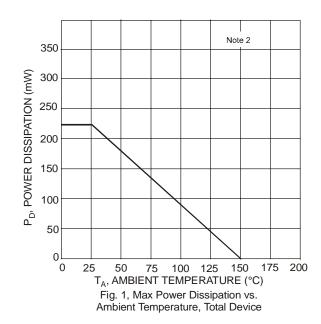


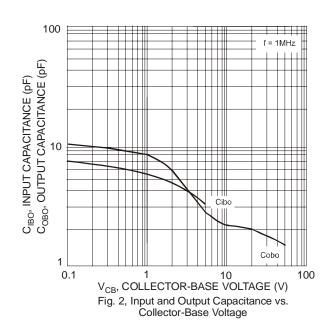
Electrical Characteristics @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Min	Max	Unit	Test Condition				
OFF CHARACTERISTICS (Note 6)									
Collector-Base Breakdown Voltage	V _{(BR)CBO}	-40	_	V	$I_C = -10\mu A, I_E = 0$				
Collector-Emitter Breakdown Voltage	V _{(BR)CEO}	-40		V	$I_C = -1.0 \text{mA}, I_B = 0$				
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	-5.0		V	$I_E = -10\mu A, I_C = 0$				
Collector Cutoff Current	I _{CEX}		-50	nA	$V_{CE} = -30V, V_{EB(OFF)} = -3.0V$				
Base Cutoff Current	I_{BL}		-50	nA	$V_{CE} = -30V, V_{EB(OFF)} = -3.0V$				
ON CHARACTERISTICS (Note 6)									
		60	_		$I_C = -100\mu A, V_{CE} = -1.0V$				
		80	_		$I_C = -1.0 \text{mA}, V_{CE} = -1.0 \text{V}$				
DC Current Gain (Note 7)	h _{FE}	100	300		$I_C = -10 \text{mA}, V_{CE} = -1.0 \text{V}$				
		60	_		$I_C = -50 \text{mA}, V_{CE} = -1.0 \text{V}$				
		30	_		$I_C = -100 \text{mA}, V_{CE} = -1.0 \text{V}$				
Collector-Emitter Saturation Voltage	V _{CE(SAT)}	_	-0.25	V	$I_C = -10mA$, $I_B = -1.0mA$				
Compositor Emiliari Cataration Voltage	V CE(SAT)		-0.40	•	$I_C = -50 \text{mA}, I_B = -5.0 \text{mA}$				
Base-Emitter Saturation Voltage	V _{BE(SAT)}	-0.65	-0.85	V	$I_C = -10 \text{mA}, I_B = -1.0 \text{mA}$				
		_	-0.95	v	$I_C = -50 \text{mA}, I_B = -5.0 \text{mA}$				
SMALL SIGNAL CHARACTERISTICS									
Output Capacitance	C _{obo}		4.5	pF	$V_{CB} = -5.0V$, $f = 1.0MHz$, $I_E = 0$				
Input Capacitance	C _{ibo}		10	pF	$V_{EB} = -0.5V$, $f = 1.0MHz$, $I_C = 0$				
Input Impedance	h _{ie}	2.0	12	kΩ					
Voltage Feedback Ratio	h _{re}	0.1	10	x 10 ⁻⁴	$V_{CE} = 10V, I_{C} = 1.0mA,$				
Small Signal Current Gain	h _{fe}	100	400	—	f = 1.0kHz				
Output Admittance	h _{oe}	3.0	60	μS					
Current Gain-Bandwidth Product	f _T	250	_	MHz	$V_{CE} = -20V$, $I_{C} = -10mA$, $f = 100MHz$				
Noise Figure	NF	_	4.0	dB	$V_{CE} = -5.0V$, $I_{C} = -100\mu A$, $R_{S} = 1.0k\Omega$, $f = 1.0kHz$				
SWITCHING CHARACTERISTICS			1	I	1.0				
Delay Time	t _d	_	35	ns	$V_{CC} = -3.0V$, $I_{C} = -10mA$,				
Rise Time	t _r	_	35	ns	$V_{BE(off)} = 0.5V, I_{B1} = -1.0mA$				
Storage Time	ts	_	225	ns	$V_{CC} = -3.0V, I_{C} = -10mA,$				
Fall Time	t _f	_	75	ns	$I_{B1} = I_{B2} = -1.0 \text{mA}$				

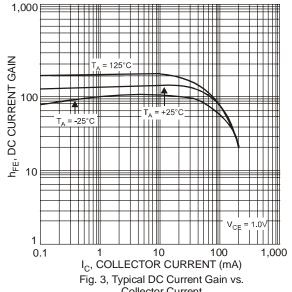
Notes:

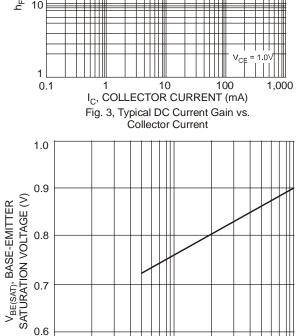
- 6. Short duration pulse test used to minimize self-heating effect.
 7. The DC current gain, h_{FE}, is matched at I_C = -10mA and V_{CE} = -1.0V with typical matched tolerances of 1% and maximum of 2%.











10 V_{CE(SAT)}, COLLECTOR-EMITTER SATURATION VOLTAGE (V) :0 0.01 10 100 I_C, COLLECTOR CURRENT (mA) 1,000

Fig. 4, Typical Collector-Emitter Saturation Voltage vs. Collector Current

Ordering Information (Note 5 & 8)

Device	Packaging	Shipping			
DMMT3906-7-F	SOT-26	3000/Tape & Reel			

Notes: 8. For packaging details, go to our website at http://www.diodes.com/datasheets/ap02007.pdf.

10 I_C, COLLECTOR CURRENT (mA) Fig. 5, Typical Base-Emitter Saturation Voltage vs. Collector Current

Marking Information

0.5



K3Q = Product Type Marking Code YM = Date Code Marking Y =Year ex: T = 2006

M = Month ex: 9 = September

Date Code Key

Year	2004	2005	2006	2007	2008	2009	2010	2011	2012
Code	R	S	Т	U	V	W	X	Υ	Z

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D



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